IDT

Integrated Device Technology, Inc.
2975 Stender Way, Santa Clara, CA - 95054

PRODUCT/PROCESS CHANGE NOTICE (PCN)

PCN #: **L0105-03** DATE: **May 24, 2001**
Product Affected: QS3VH245, QS32XVH245, QS34XVH245

Manufacturing Location Affected: N/A
Date Effective: **August 24, 2001**

MEANS OF DISTINGUISHING CHANGED DEVICES:
- ☐ Product Mark
- ☐ Back Mark
- ■ Date Code — Prefix "XQ" or "QC" to "Z"
- ☐ Other

Contact: Bimla Paul
Title: Q. A. Manager
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Attachment:: ■ Yes ☐ No

Samples: Available upon request

DESCRIPTION AND PURPOSE OF CHANGE:
- ☐ Die Technology
- ☐ Wafer Fabrication Process
- ☐ Assembly Process
- ☐ Equipment
- ☐ Material
- ☐ Testing
- ☐ Manufacturing Site
- ☐ Data Sheet
- ■ Other — Die revision from "XQ" or "QC" to "Z" stepping to enhance the device performance

RELIABILITY/QUALIFICATION SUMMARY:
There will be no impact or effect on the product reliability. The qualification data is attached.

CUSTOMER ACKNOWLEDGMENT OF RECEIPT:
IDT records indicate that you require written notification of this change. Please use the acknowledgement below or E-Mail to grant approval or request additional information. If IDT does not receive acknowledgement within 30 days of this notice it will be assumed that this change is acceptable.
IDT reserves the right to ship either version manufactured after the process change effective date until the inventory on the earlier version has been depleted.

Customer: ______________ ☐ ***Approval for shipments prior to effective date.***

Name/Date: ______________ E-Mail Address: ______________

Title: ______________ Phone# /Fax# : ______________

CUSTOMER COMMENTS: ______________

IDT ACKNOWLEDGMENT OF RECEIPT:

RECD. BY: ______________ DATE: ______________

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ATTACHMENT - PCN #: L0105-03

PCN Type: Die revision

Data Sheet Change Yes.

Following data sheet limits have been revised due to the enhanced device performance:

Test Parameter	Old Limit	New Limit
$t_{PZL/ZH}$	9 ns	7 ns
$t_{PLZ/HZ}$	8 ns	6.5 ns
$f_{\overline{OE}}$	1 MHz	20 MHz

Detail of Change The die has been revised from "XQ" and "QC" stepping to "Z" stepping to enhance the device performance.
Selective data sheet limits have been revised due to the enhanced device performance.

Die Revision Details

	Current Die Rev - XQ	Current Die Rev - QC	New Die Rev - Z
Wafer Fab Technology	0.8 µ	0.8 µ	0.8 µ
Poly Gate	0.8 µ	0.8 µ	0.8 µ
Minimum Gate Oxide Thickness	150 Å	150 Å	150 Å
Wafer Size	6 "	6 "	6 "
Fab Facility	Fab 5 (PSA, Australia)	Fab 2 (Salinas, USA)	Fab 2 (Salinas, USA)
Date Code Prefix	XQ	QC	Z

Conversion schedule (Estimated)

	Sample Availability	Production Shipments
QS3VH245	Available	08/24/01
QS32XVH245	Available	08/24/01
QS34XVH245	Available	08/24/01

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Qualification Plan QLG-01-01

Test Vehicle: QS3VH862

Qualification Test Plan and Results:

Test Description	SS/Acc #	Test Results
Dynamic High Temp Operating Life Test Mil-Std-883, Method-1005	116/0	116/0
ESD - HBM Mil-Std-883, Method-3015	3/0	3500 Volts
ESD-CDM JESD22-C101	3/0	1000 Volts
ESD-MM EIAJ-IC-121	3/0	400 Volts
Latch-up EIA/JESD78	10/0	10/0

Characterization Data:

Characterization data is available upon request.